

# Advanced Insulating Film for Next-Generation Smartphone Performance Requirements

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#### **Presentation Contents**

- 1. Brief Company Introduction of Ajinomoto Co., Inc.
- 2. Insulation Build-up Materials; Ajinomoto Build-up Film(ABF) Low Dielectric Loss ABF for high frequency package Next Generation ABF for Thinner Application
- 3. Molding Film(ABF-LE)



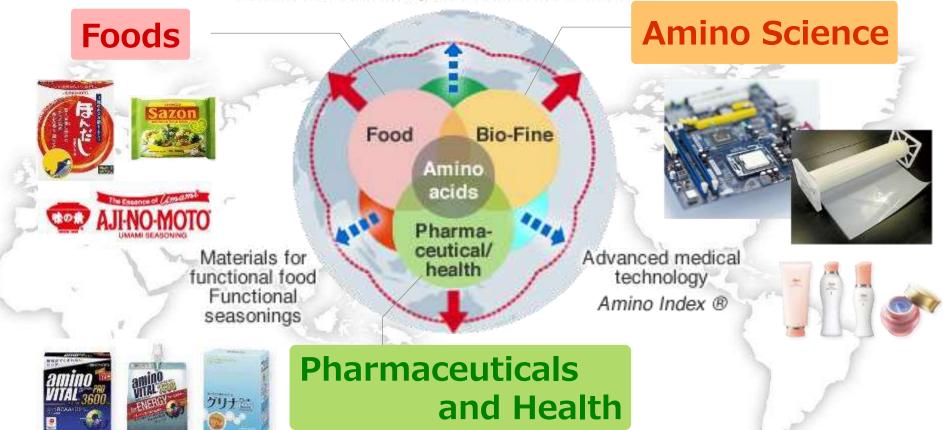


# Over View of the Ajinomoto Group

Foundation	May 20, 1909	Paid-in Capital	JPY 79,863million
Number of employee	34,452	Net sales FY2017	JPY 1,150.2 billion

(as of March 31, 2017)

Lower resource fermentation technology Nutrition for animals, plants, and marine creatures





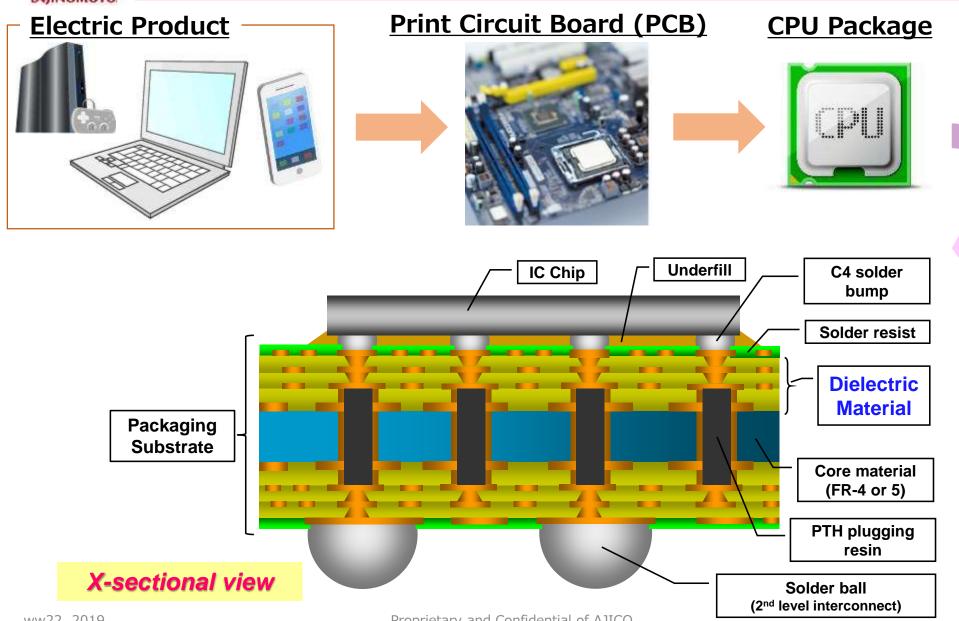


# Insulation Build-up Materials; Ajinomoto Build-up Film(ABF)





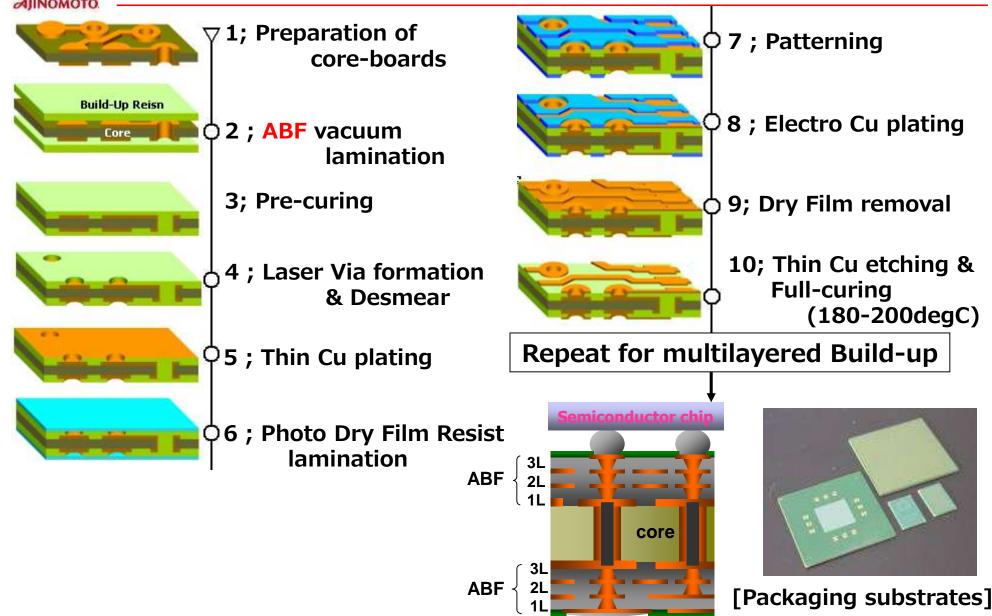
# **ABF Application**





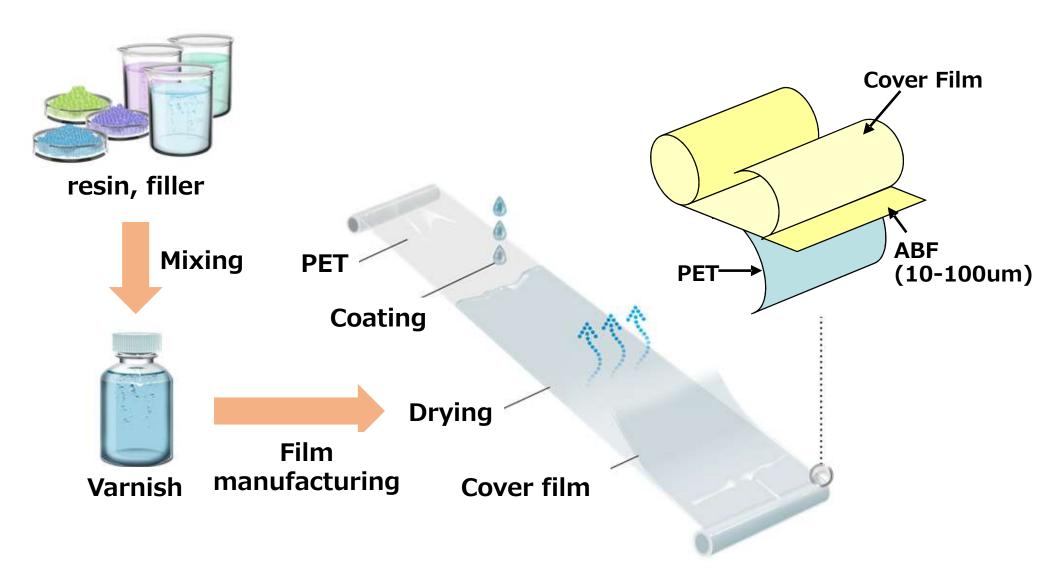


# Outline of Manufacturing Substrates using ABF



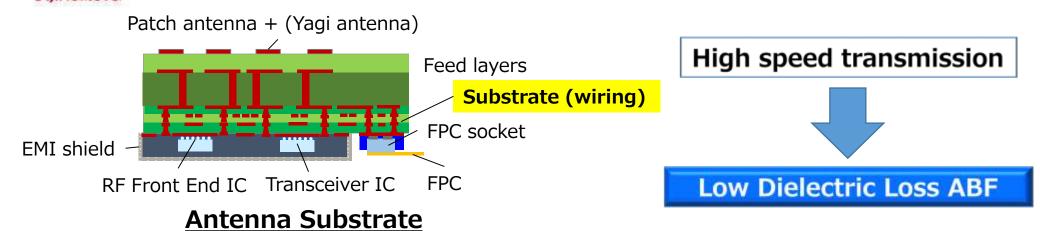


# Manufacturing Process of ABF

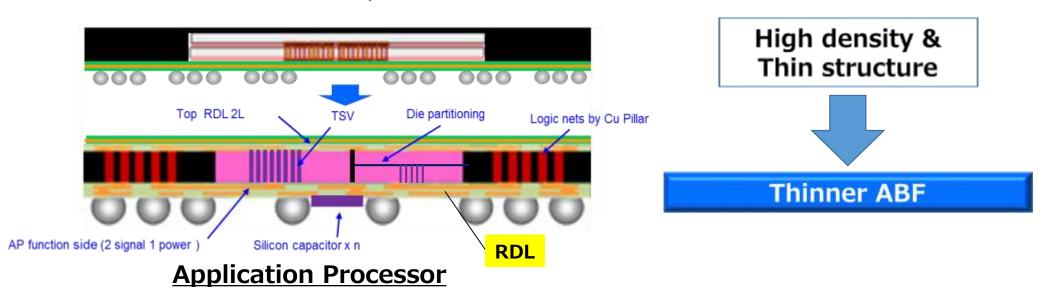




# Smartphone PKG trend & ABF development trend



FO-PLP for Wide bus memory





# Next Build-up Material for High Speed Application

### ■ Requirement for

#### **Low Transmission Loss**

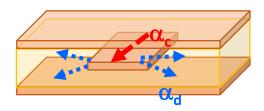
#### Transmission loss ( $\alpha$ )

Dielectric loss(α<sub>d</sub>)+ Conductor loss(α<sub>c</sub>)

$$\alpha_{d} \propto \sqrt{\epsilon} x tan\delta$$

ε: Dielectric constant

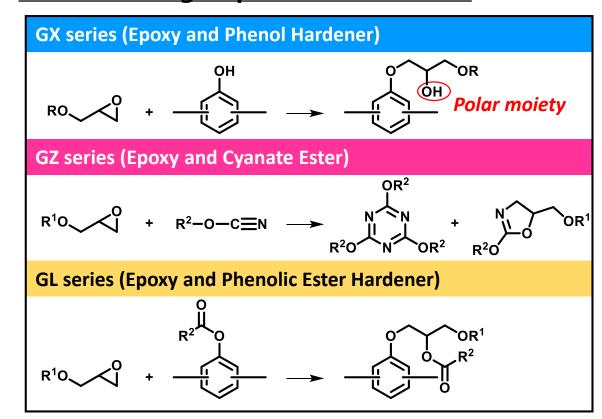
tanδ: Dielectric loss tangent



To reduce the transmission loss...

→ Low dielectric loss tangent (Df)

#### **■ ABF for High Speed Transmission**



**Reduction of polar group** 



# Outline of New ABF GL series

ABF	GX92	GX-T31	GZ41	NEW GL
CTE (ppm: 25-150degC)	39	23	20	20
Tg (degC, tensile TMA)	153	154	176	153
Dielectric constant (5.8GHz)	3.2	3.4	3.3	3.3
Loss tangent	0.018	0.014	0.0074	0.0044
ABF Surface after desmear (SEM, x3500)				

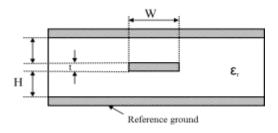




#### **Evaluation of Transmission Loss**

#### \* Formula of strip line impedance

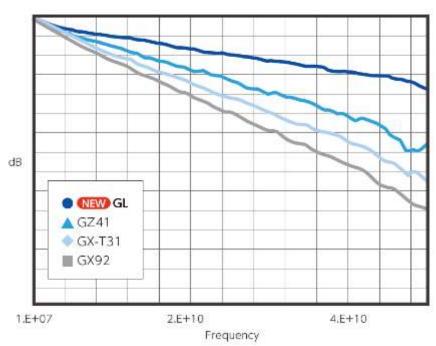
$$Z_{s} = \frac{30\pi}{\sqrt{\varepsilon_{r}}} \left[ \frac{(2H+t)}{(W+0.441(2H+t))} \right]$$

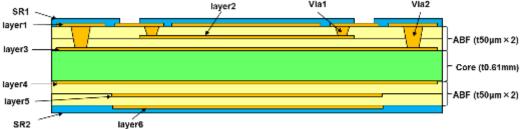


W: 45-50um 2H: 80um

t: 13-23um

 $Z_S$ : 50 $\Omega$ 





Cross sectional view image of PKG

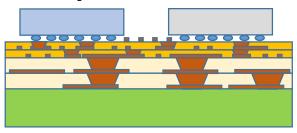
**Transmission Loss:** GX92 >> GX-T31 > GZ41 > GL

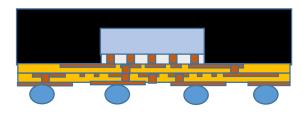
Low Df material shows lower transmission loss.



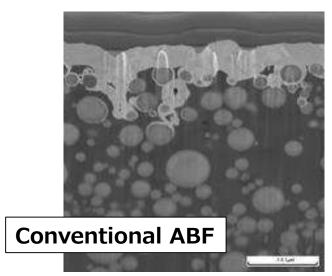
# Next Generation ABF for Thinner Application

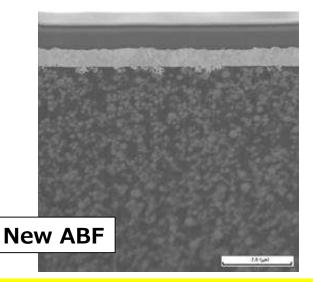
#### ■ Redistribution layer of 2.1D / Fan-out package





- ✓ Thinner LtL, Smaller via, Finer Line & Space → Using Smaller Silica
- Development of New ABF with smaller Silica



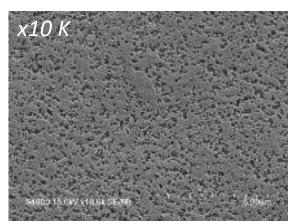


New ABF with smaller silica showed smooth surface after E-less Cu plating

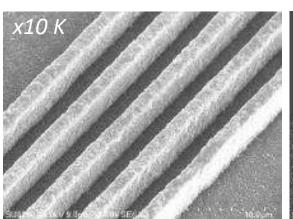


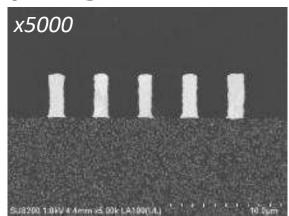
#### Fine Line & Fine Via Formation

#### **After Wet desmear**



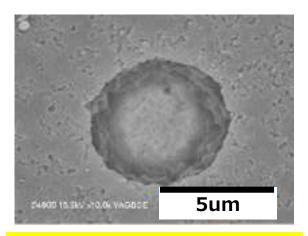
#### **After Cu plating**





13

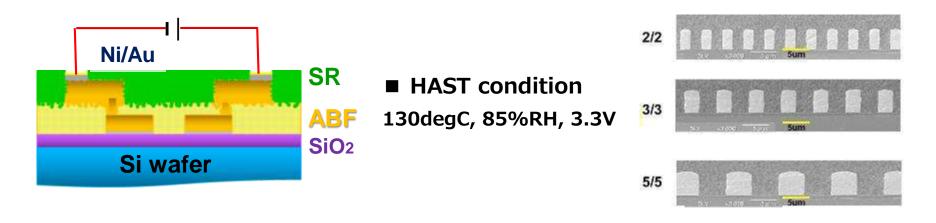
Smoother surface  $\rightarrow$  L/S = 2/2 by SAP



**♦5um via by UV Laser** 



# Insulation reliability (Line to Line)



ABF	L/S=2/2um	L/S=3/3um	L/S=5/5um
GX92	NG	150hrs pass	200hrs pass
GX-T31	NG	200hrs pass	200hrs pass
New ABF with smaller Silica	200hrs pass	200hrs pass	200hrs pass

New ABF with smaller silica keeps good insulation even L/S = 2um / 2um.



# Molding Film





# Background

#### Market expectation for Fan-out WLCSP

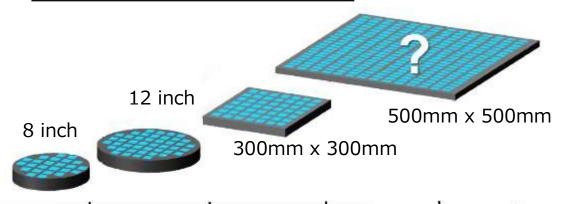
# Fan-in WLCSP Fan-out WLCSP

- Advantages over fan-in WLCSP
- ✓ No pad pitch restriction due to fan-out area
- ✓ Only KGD is packaged!
- ✓ Potential SiP integration
- ✓ Lower thermal resistance

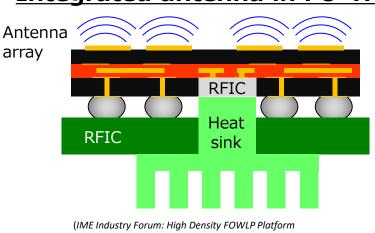
FC-BGA

- Advantages over FC-BGA
- ✓ Thinner
- ✓ Shorter inter connection due to substrate-less
- ✓ Future potential for SiP / 3D integration
- ✓ Lower thermal resistance

#### Wafer form to Panel form



#### ■ Integrated antenna in FO-WLP







# Characteristics of Sheet Molding Compound

Material Name	LE	
CTE (30-150degC)(ppm/K)		<15
CTE (50-150degC)(ppm/K)	TMA	<15
CTE (150-240degC)(ppm/K)		<25
Young's modulus (GPa)	<b>T</b>	<15
Breaking strength (MPa)	Tensile mode	50
Elongation (%)	mode	>1.0
Dielectric constant (Dk)	Cavity	3.2~3.3
Dissipation factor (Df)	Perturbation method @5.8GHz	<0.01
Peel strength (kgf/cm)	Cu Plating	0.4~0.5
x-y HAST L/S=15/15um	130degC, 85%, 3.3V	>200h

•Low CTE & Low Young's Modulus

⇒ No warpage after the one-side
resin curing

LE: No warpage!

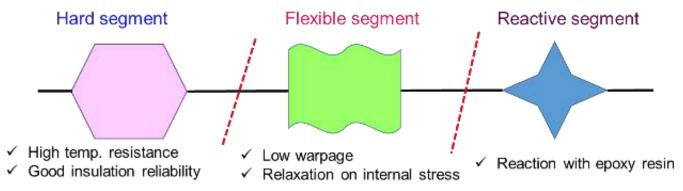


GX13:Big warpage!

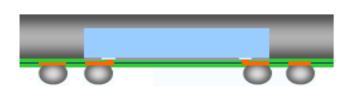


(Laminated on 4 inches φ Si wafer)

- •Low Df value
- •Good insulation reliability



Suitable for Molding Material!





# Summary

### 1. Advanced Build-up Materials; Next Generation ABF

Low Dielectric Loss ABF

Lower Df ABF showed lower transmission loss

- >> Applicable to high frequency packages
- Next Generation Material for Thinner Application

Good Processability & Insulation Reliability

>> Applicable to WLP/PLP redistribution layer and thinner packages

### Molding Film (ABF-LE)

Low Warpage, Good HAST Reliability, and Low Loss Tangent

>> Suitable for FO-WLP/PLP

# Eat Well, Live Well.





Thank you very much for your attention!